

# 深圳市晶泰源电子有限公司

## 2SA1201 TRANSISTOR (PNP)

### FEATURES

- High voltage
- High transition frequency
- Complementary to 2SC2881

### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

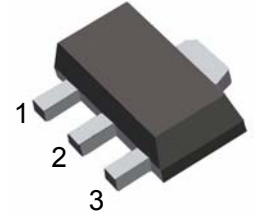
Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.8	A
$P_C$	Collector Power Dissipation	0.5	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$

### SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-120\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			30	pF

### CLASSIFICATION OF $h_{FE}$

Rank	O	Y
Range	80-160	120-240
Marking	DO	DY